



SOT-23 Plastic-Encapsulate Diodes

1SS196

SWITCHING DIODE

FEATURES

Power dissipation

P_D : 150 mW ($T_{amb}=25^{\circ}C$)

Forward Current

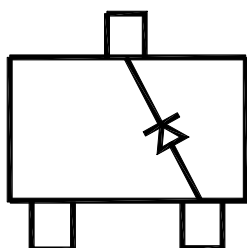
I_F : 100 mA

Reverse Voltage

V_R : 80 V

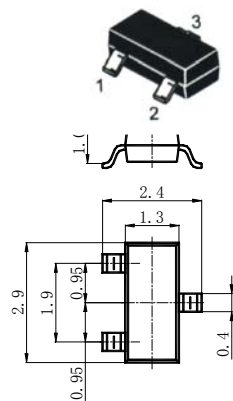
Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



Marking G3

SOT—23



Unit : mm

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	80		V
Reverse voltage leakage current	I_R	$V_R=80V$		0.5	μA
Forward voltage	V_F	$I_F=100mA$		1.2	V
Diode capacitance	C_D	$V_R=0V$ $f=1MHz$		4	pF
Reverse recovery time	t_{rr}			4	nS